

10/582860

S/N: TBA

06/14/2006 IAP2011CCD PCT/PTG-1493 JUN 2006
Docket No: PCT/PTG-1493 JUN 2006

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Serial No.: TO BE ASSIGNED Confirmation No.: TO BE ASSIGNED
Applicant: Toru YAMADA et al. Art Unit: TO BE ASSIGNED
Filed: June 14, 2006 Examiner: TO BE ASSIGNED
Docket No: SUG-193-PCT Customer No: 28892
For: Vapor Phase Growth Apparatus and Method of Fabricating
Epitaxial Wafer

INFORMATION DISCLOSURE STATEMENT
PURSUANT TO 37 C.F.R. §§ 1.56, 1.97, and 1.98

US Patent & Trademark Office
Customer Service Window
Randolph Building
401 Dulany Street
Alexandria, VA 22314

Sir:

In compliance with the dictates of 37 C.F.R. §§ 1.56, 1.97, and 1.98, Applicant hereby submits an Information Disclosure Statement.

Three of the attached seven documents are mentioned in the present specification and a brief description of their relevance can be found therein.

Applicant hereby reports the issuance of a Search Report in the corresponding Japanese application. A copy of that Search Report and two of the references cited therein (noted on attached PTO Form 1449) is attached hereto.

10/582860

14 JUN 2006
Docket No.: SUG-193-PCT

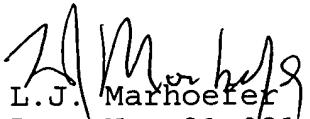
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INFORMATION DISCLOSURE STATEMENT TRANSMITTAL - PAGE 2 of 2

It is respectfully requested that the Examiner consider each of these references and indicate such consideration by enclosing an appropriately initialled copy of the enclosed form PTO-1449 with the next communication from the Patent Office.

Respectfully submitted,


L.J. Marhoefer
Reg. No. 21,091
Signing for
Ronald R. Snider
Attorney of Record
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Date: June 14, 2006

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AP20RecdPCT/PTO 14 JUN 2006

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INFORMATION DISCLOSURE STATEMENT - PTO FORM 1449

FOREIGN PATENT DOCUMENTS				
Examiner Initials*	Foreign Patent Document Number	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T**
	JP 2002-231641 w/ English Abstract	Shinetsu Handotai KK Nagano Electronics Ind	08-16-2002	
	JP 2002-198316 w/ English Abstract	Shinetsu Handotai KK Nagano Electronics Ind	07-12-2002	
	JP 2001-44125 w/ English Abstract	Applied Materials Inc	02-16-2001	
	JP 2000-331939 w/ English Abstract	Applied Materials Inc	11-30-2000	
	JP 7-193015	Applied Materials Inc	07-28-1995	X
	EP 0 637 058 A1	Applied Materials Inc	02-01-1995	
	EP 0 637 058 B1	Applied Materials Inc	02-01-1995	

Examiner Signature		Date Considered	
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*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

**Applicant is to place a check mark here if English language translation is attached